



High-Quality, Single-Crystalline Silicon-Germanium Films

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The Invention

High-quality, single-crystalline silicon-germanium ($\text{Si}(1-x)\text{Ge}_x$) having a high germanium content is provided. Layers of the high-quality, single-crystalline silicon-germanium can be grown to high sub-critical thicknesses and then released from their growth substrates to provide $\text{Si}(1-x)\text{Ge}_x$ films without lattice mismatch-induced misfit dislocations or a mosaic distribution of crystallographic orientations.

Additional Information

For More Information About the Inventors

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Tech Fields

- [Semiconductors & Integrated Circuits : Components & materials](#)

For current licensing status, please contact Jeanine Burmania at jeanine@warf.org or 608-960-9846